**Product data sheet** 

## 1. Product profile

### 1.1 General description

Planar passivated high commutation three quadrant triac in a SOT428 (DPAK) surface-mountable plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

### 1.2 Features and benefits

- 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- High commutation capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface-mountable package
- Triggering in three quadrants only

### 1.3 Applications

- AC solenoids
- General purpose motor control
- Home appliances

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25$ °C; $t_p = 20$ ms; see Figure 4; see Figure 5	-	-	25	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 107 ^{\circ}\text{C}$ ; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	4	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{ Company of the compan$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{I}}$	-	-	10	mA

# 2. Pinning information

Table 2. Pinning information

	_			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		<b>N</b> .
2	T2	main terminal 2	mb	T2 T1
3	G	gate		`G sym051
mb	T2	mounting base; main terminal 2	1 3	
			SOT428 (DPAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA204S-800E	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

IGMpeak gate current-2APGMpeak gate power-5W						
$\begin{array}{llllllllllllllllllllllllllllllllllll$	Symbol	Parameter	Conditions	Min	Max	Unit
$I_{TSM}  \text{non-repetitive peak on-state}  \text{full sine wave; $T_{j(init)} = 25  ^{\circ}\text{C}$; $t_p = 20  \text{ms;}}  -  25  \text{A}  \text{see Figure 4; see Figure 5}  \text{full sine wave; $T_{j(init)} = 25  ^{\circ}\text{C}$; $t_p = 16.7  \text{ms}}  -  27  \text{A}  \text{I}^{2}\text{t}  \text{I}^{2}\text{t for fusing}  t_p = 10  \text{ms; sine-wave pulse}  -  3.1  \text{A}^{2}\text{s}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; $I_G = 0.2  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; I}_{G} = 0.2  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; I}_{G} = 0.2  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; I}_{G} = 0.2  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; I}_{G} = 0.2  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; I}_{G} = 0.2  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; I}_{G} = 0.2  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{A/µs}}  -  100  \text{A/µs}  \text{I}^{2}\text{model}  \text{II}_{T} = 6  \text{A; dI}_{G}/\text{dt} = 0.2  \text{A/µs}}  -  100  \text{A/µs}  \text{A/µs}}  -  100  \text{A/µs}  \text{A/µs}}  -  100  \text{A/µs}  \text{A/µs}}  -  100  \text{A/µs}  \text{A/µs}}  -  100  \text{A/µs}}  -  100 $	$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	I <sub>T(RMS)</sub>	RMS on-state current		-	4	Α
$I^2t$ $I^2t$ for fusing $t_p = 10$ ms; sine-wave pulse-3.1 $A^2s$ $dI_T/dt$ rate of rise of on-state current $I_T = 6$ A; $I_G = 0.2$ A; $dI_G/dt = 0.2$ A/μs-100 $A/μs$ $I_{GM}$ peak gate current-2A $P_{GM}$ peak gate power-5W $P_{G(AV)}$ average gate powerover any 20 ms period-0.5W $T_{stg}$ storage temperature-40150°C	I <sub>TSM</sub>			-	25	Α
dI <sub>T</sub> /dt rate of rise of on-state current I <sub>T</sub> = 6 A; I <sub>G</sub> = 0.2 A; dI <sub>G</sub> /dt = 0.2 A/ $\mu$ s - 100 A/ $\mu$ s I <sub>GM</sub> peak gate current - 2 A P <sub>GM</sub> peak gate power - 5 W P <sub>G(AV)</sub> average gate power over any 20 ms period - 0.5 W T <sub>stg</sub> storage temperature -40 150 °C			full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms	-	27	Α
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	3.1	A <sup>2</sup> s
$P_{GM}$ peak gate power - 5 W $P_{G(AV)}$ average gate power over any 20 ms period - 0.5 W $T_{stg}$ storage temperature -40 150 °C	dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 6 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
P <sub>G(AV)</sub> average gate power over any 20 ms period - 0.5 W T <sub>stg</sub> storage temperature -40 150 °C	$I_{GM}$	peak gate current		-	2	Α
T <sub>stg</sub> storage temperature -40 150 °C	$P_{GM}$	peak gate power		-	5	W
sig conformation	P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>j</sub> junction temperature - 125 °C	T <sub>stg</sub>	storage temperature		-40	150	°C
	Tj	junction temperature		-	125	°C

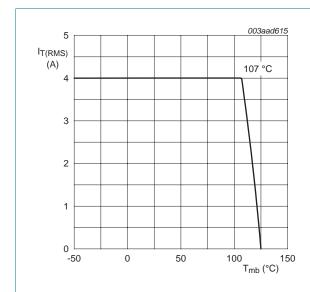
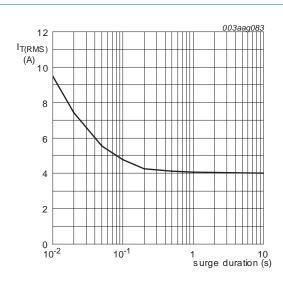


Fig 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{\text{mb}} = 107 \text{ °C}$ 

Fig 2. RMS on-state current as a function of surge duration; maximum values

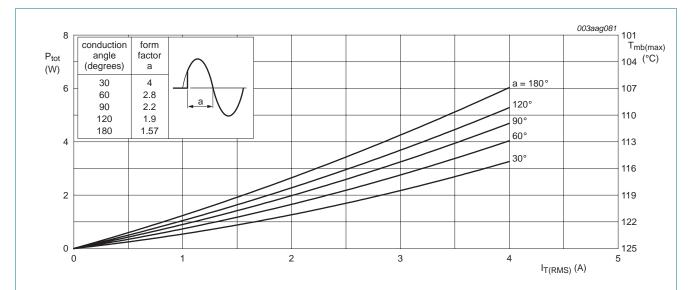
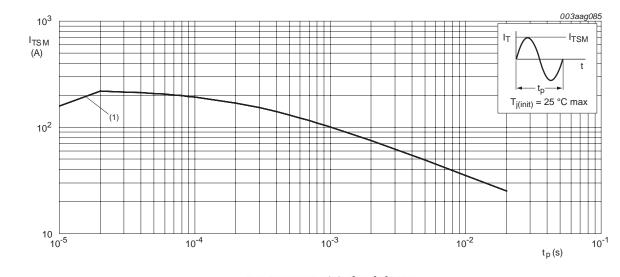


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_{\text{p}}~\leq~20~ms;~~(1)~dI_{\text{T}}/dt~limit$ 

Fig 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

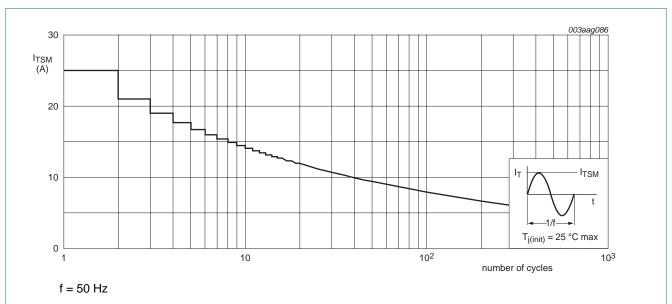


Fig 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to	full cycle; see Figure 6	-	-	3	K/W
	mounting base	half cycle; see Figure 6	-	-	3.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; printed circuit board (FR4) mounted	-	75	-	K/W

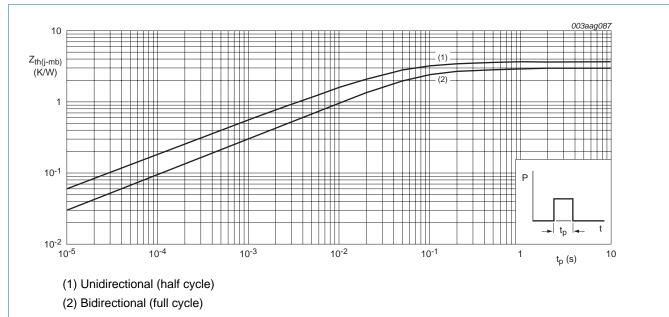
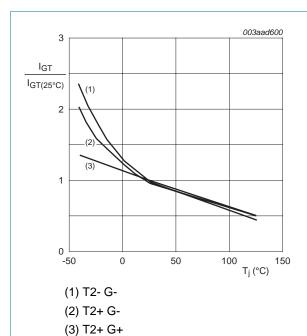


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+G+; T_j = 25 \text{ °C;}$ see Figure 7	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-; T_j = 25 \text{ °C;}$ see Figure 7	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- G-; } T_j = 25 \text{ °C;}$ see Figure 7	-	-	10	mA mA mA mA V V V MA V/ µs
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 8}}{}$	-	-	12	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ \text{ G-; } T_j = 25 \text{ °C; } $ see Figure 8	-	-	18	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- G-; } T_j = 25 \text{ °C; } $ see Figure 8	-	-	12	mA
l <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	-	12	mΑ
V <sub>T</sub>	on-state voltage	$I_T = 5 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 10	-	1.4	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ see Figure 11	0.25	0.4	-	mA mA mA MA V V V MA V/ µs
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mΑ
Dynamic o	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; exponential waveform; gate open circuit	30	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 4 \text{ A};$ $dV_{com}/dt = 0.1 \text{ V/}\mu\text{s};$ gate open circuit	8	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 4 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; \text{ gate open circuit}$	2.1	-	-	A/ms
gt	gate-controlled turn-on time	$I_{TM} = 12 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs



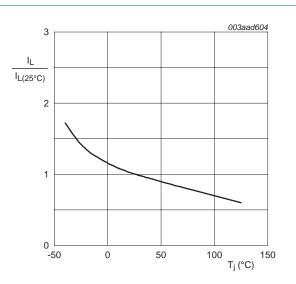
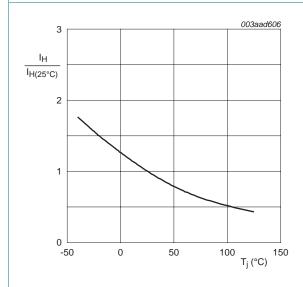
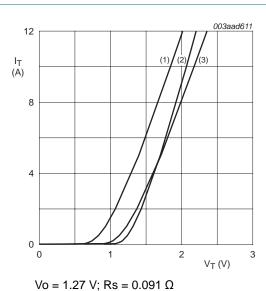


Fig 7. Normalized gate trigger current as a function of junction temperature

Fig 8. Normalized latching current as a function of junction temperature



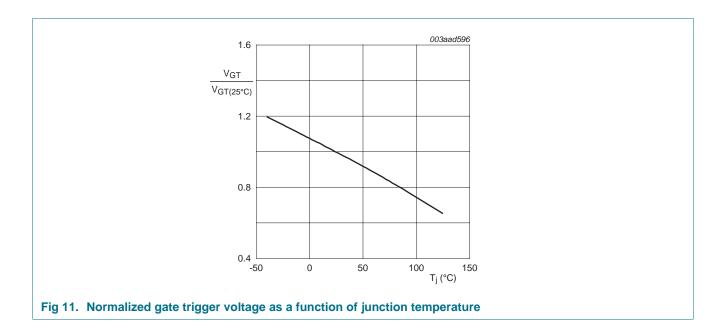


(1) Tj = 125 °C; typical values(2) Tj = 125 °C; maximum values

(3) Tj = 25 °C; maximum values

Fig 9. Normalized holding current as a function of junction temperature

Fig 10. On-state current as a function of on-state voltage



## 7. Package outline

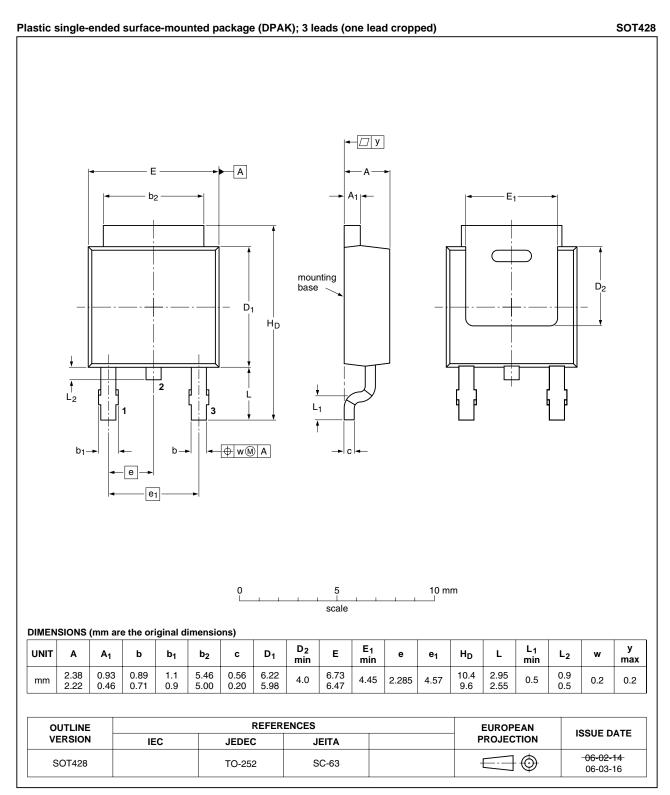


Fig 12. Package outline SOT428 (DPAK)

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BTA204S-800E v.6	20110510	Product data sheet	-	BTA204S_SER_D_E_F v.5	
Modifications:		ormat of this data sheet has been redesigned to comply with the new identity lines of NXP Semiconductors.			
	<ul> <li>Legal texts h</li> </ul>	ave been adapted to the	new company name	where appropriate.	
	<ul> <li>Type number</li> </ul>	r BTA204S-800E separate	ed from data sheet	BTA204S_SER_D_E_F v.5.	
BTA204S_SER_D_E_F v.5	20060216	Product data sheet	-	BTA204S_SER_D_E_F v.4	

## 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BTA204S-800E

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BTA204S-800E

**3Q Hi-Com Triac** 

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For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

## 11. Contents

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